BAV101 ~ BAV103

SMALL SIGNAL SWITCHING DIODE

FEATURES

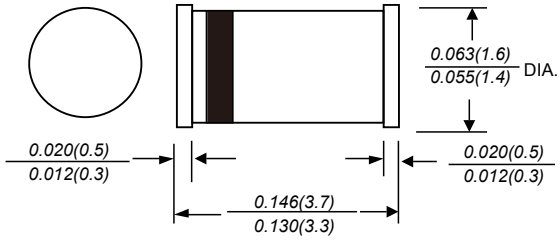
- Silicon epitaxial planar diode
- Fast switching diodes
- 300mw power dissipation
- High temperature soldering guaranteed 250℃/10S at terminals

MECHANICAL DATA

Case: MINI MELF glass sealed envelope.
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight:0.002 ounce, 0.05 grams

RoHS Compliant

MINI MELF (LL-34)



Dimensions in inches and (millimeters)

Maximum Ratings (T_A=25°C Unless otherwise noted)

PARAMETER	SYMBOL	BAV101	BAV102	BAV103	UNITS
Reverse Voltage	V_R	100	150	200	V
Peak Reverse Voltage	V_{RRM}	120	200	250	V
Rectified Current (Average), Half Wave Rectification with Resistive Load and f >=50 Hz	I_O	200			mA
Peak Forward Surge Current, t=1000ms	I_{FSM}	1.0			A
Power Dissipation Derate Above at 25°C	P_D	300			mW
Maximum Forward Voltage, I_F = 100mA	V_F	1.0			V
Maximum DC Reverse Current at Rated DC Blocking Voltage T_J= 25°C	I_R	0.1			μA
Typical Junction Capacitance(Note 1)	C_J	3.0			pF
Maximum Reverse Recovery (Note 2)	t_{rr}	75			ns
Typical Thermal Resistance	$R_{\theta JA}$	350			°C / W
Operation Junction Storage Temperature Range	T_{STG}	-65 to +175			°C

NOTE:
1. CJ at V_R=0, f=1MHZ
2. From I_F=10mA to I_R=-1mA, V_R=6Volts, R_L=100Ω

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RATINGS AND CHARACTERISTIC CURVES

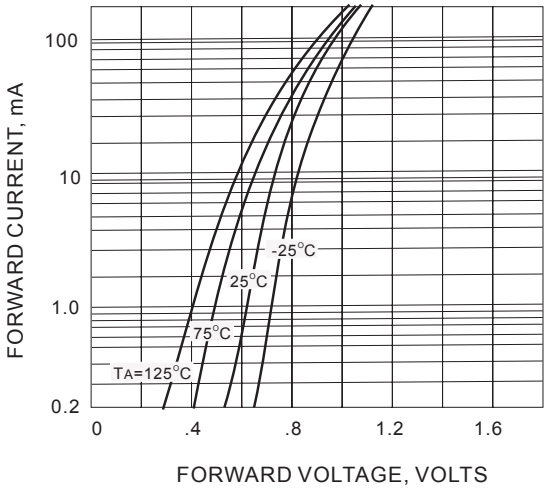

Fig.1 FORWARD CHARACTERISTICS

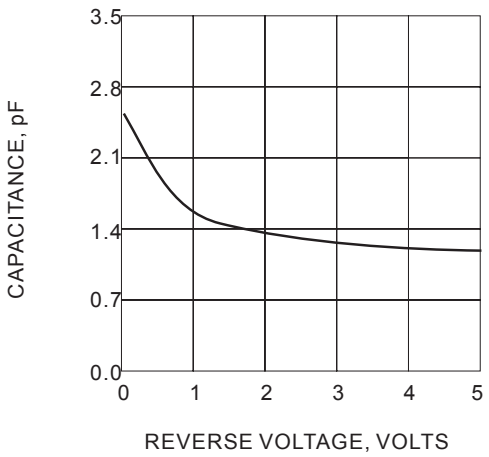

Fig.2 TYPICAL CAPACITANCE vs REVERSE VOLATGE

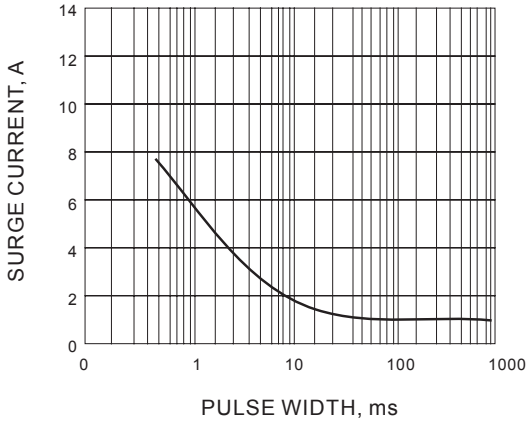

Fig. SURGE CURRENT CHARACTERISTIC